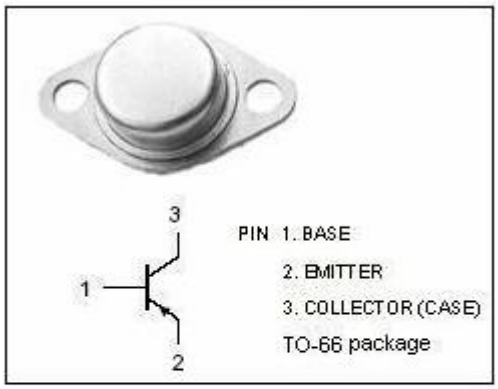
isc Silicon PNP Power Transistor 2N6420

DESCRIPTION

- Contunuous Collector Current-I_C= -1A
- Power Dissipation-P_C= 35W @T_C= 25℃
- Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= -5.0 V(Max)@ I_C = -1A



APPLICATIONS

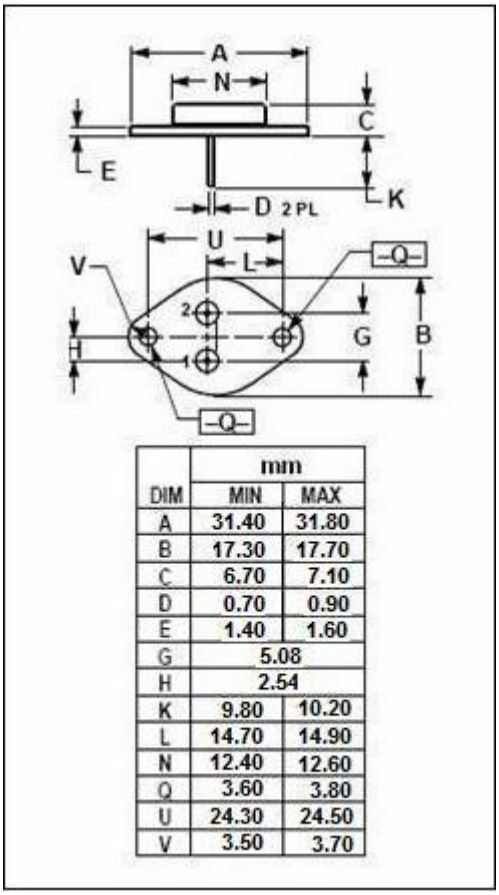
- Designed for high-speed switching and linear amplifier application for high-voltage operational amplifiers, switching regulators, converters,deflection stages and high fidelity amplifiers.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-250	V
V_{CEO}	Collector-Emitter Voltage	-175	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-1.0	A
I_{CM}	Collector Current-Peak	-5.0	A
I_B	Base Current	-1.0	A
P_C	Collector Power Dissipation@T_C=25℃	35	W
T_J	Junction Temperature	200	℃
T_{stg}	Storage Temperature	-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	5.0	℃/W



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -50mA ; I_B= 0	-175		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1A; I_B= -0.125A		-5.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -1A ; V_{CE}= -10V		-1.4	V
I_{CEO}	Collector Cutoff Current	V_{CE}= -150V; I_B= 0		-10	mA
I_{CEX}	Collector Cutoff Current	V_{CE}= -225V; $V_{BE(off)}$= -1.5V V_{CE}= -225V; $V_{BE(off)}$= -1.5V,T_C=150℃		-1.0 -3.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C= 0		-5.0	mA
h_{FE-1}	DC Current Gain	I_C= -0.1A ; V_{CE}= -10V	40		
h_{FE-2}	DC Current Gain	I_C= -0.5A ; V_{CE}= -10V	40	200	
h_{FE-3}	DC Current Gain	I_C= -1A ; V_{CE}= -10V	10		